

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Document Number (Optional) TSMC-02-066 Applicant Chi-Chun Chen et al.	Alpha-numeric number 10/600,393 Filing Date 06/20/03 Drawn At Date 28/22
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U. S. PATENT DOCUMENTS

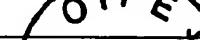
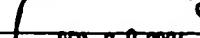
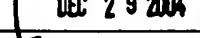
FOREIGN PATENT DOCUMENTS

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EXAMINER	DATE CONSIDERED
J. M. Thomas	19-19-14

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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In place of PTO-1449 Form		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		DEC 2 0 2004	Complete if Known
<p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i></p>					
SHEET	1	OF	1	ATTY/DOCKET NO.	2002-0066 / 24061.461
					
					
					
					
					
					
					

OTHER PRIOR ART					
Examiner's Initials	Cite No.	Include name of the author(s) (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume, issue number(s), publisher, city/country where published			
JMJ	AH	G. LUCOVSKY et al., "Formation of thin film dielectrics by remote plasma-enhanced chemical-vapor deposition (remote PECVD)", Applied Surface Science, Volume 39, Issue 1-4, October 1989, Pages 33-36.			
JMJ	AI	STANLEY WOLF et al., "Silicon Processing For The VLSI Era, Volume 1: Process Technology", Lattice Press, Sunset Beach, CA, 3 pages			
JMJ	AJ	HOWARD CHIH-HAO WANG et al., "Hot Carrier Reliability Improvement by Utilizing Phosphorus Transient Enhanced Diffusion for Input/Output Devices of Deep Submicron CMOS Technology", IEEE Electronic Device Letters, Vol. 21, No. 12, December 2000, 2 pages			
JMJ	AK	HOWARD CHIH-HAO WANG et al., "Arsenic/Phosphorus LDD Optimization by Taking Advantage of Phosphorus Transient Enhanced Diffusion for High Voltage Input/Output CMOS Devices", IEEE Transactions on Electron Devices, Volume 49, No. 1, January 2002, 5 pages.			

T. M. Thomas

03/18/05